

METHOD FOR FABRICATING A NITRIDED SILICON-OXIDE GATE DIELECTRIC

Abstract

A method of fabricating a gate dielectric layer, including: providing a substrate; forming a silicon dioxide layer on a top surface of the substrate; performing a plasma nitridation in a reducing atmosphere to convert the silicon dioxide layer into a silicon oxynitride layer. The dielectric layer so formed may be used in the fabrication of MOSFETs.